

Amendments to the Claims

This listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Original) A microelectronic device, comprising:

a microelectronic die having an active surface, a back surface, and at least one side;

said at least one microelectronic die side comprising at least one beveled sidewall and at least one channel sidewall, wherein said at least one beveled sidewall extends between said channel sidewall and said microelectronic die back surface; and

a metallization layer disposed on said microelectronic die back surface and said at least one beveled sidewall.
2. (Original) The microelectronic device of claim 1, wherein said at least one beveled sidewall is between about 30 degrees and about 60 degrees from said at least one channel sidewall.
3. (Original) The microelectronic device of claim 2, wherein said at least one beveled sidewall is about 45 degrees from said at least one channel sidewall.

4. (Original) The microelectronic device of claim 1, wherein said metallization layer is at least one metal selected from the group consisting of gold, silver, chromium, titanium, nickel vanadium, and nickel.

5. (Original) A microelectronic device assembly, comprising:
a microelectronic die having an active surface, a back surface, and at least one side;
said at least one microelectronic die side comprising at least one beveled sidewall and at least one channel sidewall, wherein said at least one beveled sidewall extends between said channel sidewall and said microelectronic die back surface;
a metallization layer disposed on said microelectronic die back surface and said at least one beveled sidewall; and
a heat dissipation device attached to said microelectronic die back surface with a thermal interface material.

6. (Original) The microelectronic device of claim 5, wherein said at least one beveled sidewall is between about 30 degrees and about 60 degrees from said at least one channel sidewall.

7. (Original) The microelectronic device of claim 6, wherein said at least one beveled sidewall is about 45 degrees from said at least one channel sidewall.

8. (Original) The microelectronic device assembly of claim 5, wherein said metallization layer is at least one metal selected from the group consisting of gold, silver, chromium, titanium, tungsten, vanadium, and nickel.

9. (Original) The microelectronic device assembly of claim 5, wherein said thermal interface material is selected from the group consisting of lead, tin, indium, silver, copper, and alloys thereof.

10. (Original) The microelectronic device assembly of claim 5, wherein at least a portion of a fillet of said thermal interface material extend from said metallization layer on said microelectronic die beveled sidewall to said heat dissipation device.

11-24. (Canceled)